

**AMENDMENT AND RESPONSE**

Serial Number: 08/636,069

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Title: METHOD TO REDUCE FIXED CHARGE IN CVD OZONE DEPOSITED FILMS

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Dkt: 303.573US1

51. (Once amended) A method of depositing a silicon dioxide layer on a substrate surface, comprising:  
contacting the substrate surface with a reaction volume of gas comprising a SiO<sub>2</sub> precursor and ozone; [and]  
heating the substrate surface to a temperature of about 480°C to 700°C; and  
illuminating the reaction volume of gas from a light source comprising mercury arc vapor lamps without directly exposing the substrate surface to the light source.
52. (Once amended) A method of depositing a doped silicon dioxide layer on a substrate surface, comprising:  
contacting the substrate surface with a reaction volume of gas comprising a SiO<sub>2</sub> precursor, ozone and at least one dopant source; [and]  
heating the substrate surface to a temperature of about 480°C to 700°C; and  
illuminating the reaction volume of gas from a light source comprising mercury arc vapor lamps without directly exposing the substrate surface to the light source.

**REMARKS**

Applicant has carefully reviewed and considered the Office Action mailed on June 15, 1999, and the references cited therewith.

Claims 31, 42, 51 and 52 are amended. Claims 1, 2, 4-10 and 31-54 are now pending in the application.

**Rejections Under 35 U.S.C. § 103****Claims 31, 33, 34, 36, 39, 40 and 42**

Claims 31, 33, 34, 36, 39, 40 and 42 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Hisamune (JP 2-050966).

Claims 31 and 42 have been amended to recite heating the substrate surface to a temperature of about 480°C to 700°C. Applicant respectfully submits that support for the